

Please amend the specification as follows:

In the Claims:

18. (amended) An apparatus comprising a semiconductor device which includes:

laterally spaced first and second sections with respective upwardly facing first and second surface portions thereon;

a third section projecting upwardly beyond each of said first and second surface portions from a location therebetween, said third section having two side surfaces on opposite sides thereof;

a substantially planar insulating layer which has portions disposed over said first and second surface portions, said third section extending into said insulating layer, and said insulating layer having first and second recess portions which respectively extend downwardly through said insulating layer toward said first and second surface portions on opposite sides of said third section, each said recess portion being immediately adjacent a respective said side surface of said third section;

a first portion of conductive material disposed in said first recess portion;

and

a second portion of conductive material disposed in said second recess portion.

Please add the following new claims:

31. The apparatus of Claim 18, wherein said side surfaces of said third section comprise an insulator, said insulator different from said substantially planar insulating layer.

32. The apparatus of Claim 31, wherein said insulator is nitride and said substantially planar insulating layer is oxide.

33. The apparatus of Claim 23, further comprising a substantially planar insulating layer coplanar with said insulating layer covering said top portion of said control terminal, wherein said control terminal and said first and second terminals are within an opening in said substantially planar insulating layer.

34. The apparatus of Claim 33, wherein said insulating layer covering said side portions and said top portion of said control terminal is nitride and said substantially planar insulating layer is oxide.

35. The integrated circuit of Claim 27, further comprising a substantially planar insulating layer coplanar with said insulating material covering said side and top portions of said gate stack, wherein said gate stack and said local interconnection terminals are within an opening in said substantially planar insulating layer.

36. The apparatus of Claim 35, wherein said insulating layer material covering said side and top portions of said gate stack is nitride and said substantially planar insulating layer is oxide.

REMARKS

Reconsideration of the above-referenced application in view of the amendments and the following remarks is respectfully requested.

The Office Action indicates that only Claims 18-22 were pending in this application. However, Applicant submitted a Preliminary Amendment at the time of filing of the instant application in which Claims 23-30 were added. A copy of the Preliminary Amendment, as well as copies of the returned postcard and